



شبكة المعلومات الجامعية

بِسْمِ اللَّهِ الرَّحْمَنِ الرَّحِيمِ





شبكة المعلومات الجامعية



شبكة المعلومات الجامعية

التوثيق الالكتروني والميكرو فيلم

جامعة عين شمس

التوثيق الالكتروني والميكرو فيلم

قسم

نقسم بالله العظيم أن المادة التي تم توثيقها وتسجيلها
علي هذه الأفلام قد اعدت دون أية تغيرات



يجب أن

تحفظ هذه الأفلام بعيداً عن الغبار

في درجة حرارة من 15 – 20 مئوية ورطوبة نسبية من 20-40 %

To be kept away from dust in dry cool place of
15 – 25c and relative humidity 20-40 %



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بعض الوثائق الأصلية تالفة



شبكة المعلومات الجامعية



بالرسالة صفحات
لم ترد بالأصل



***Study of Structural Defects in Ternary Chalcopyrite
Semiconductors by Positron Annihilation Spectroscopy
and Photoluminescence Spectroscopy***

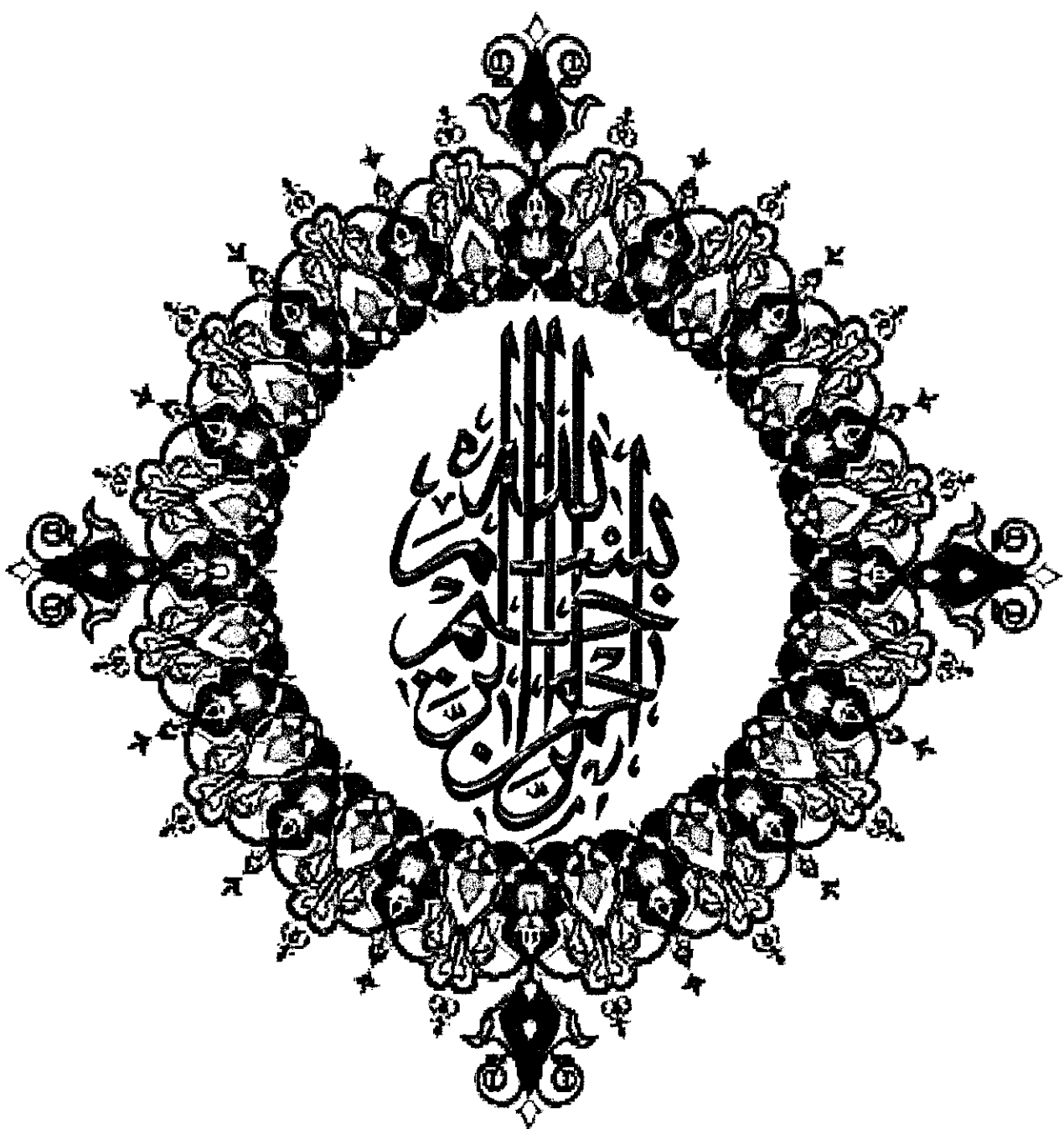
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In
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Ain Shams University

By
Mohamed Sherif Al-Kotb
B. Sc. (Physics & Computer Science) 1985
M. Sc. (Physics) 1994

2000

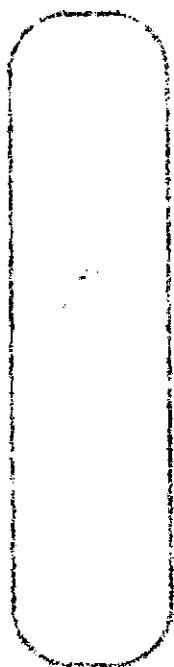
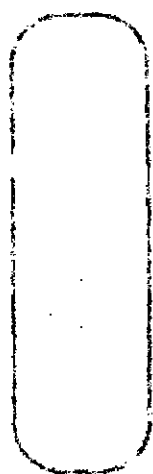
B N O E K



*To My Sons
Omar and Khaled*



THE
HISTORICAL SOCIETY



Author



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